MSKSEMI 美森科













ESD

TSS

MOV

GDT

PIFD

BAS70/-04/-05/-06

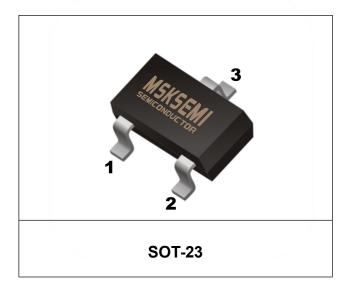
Product specification



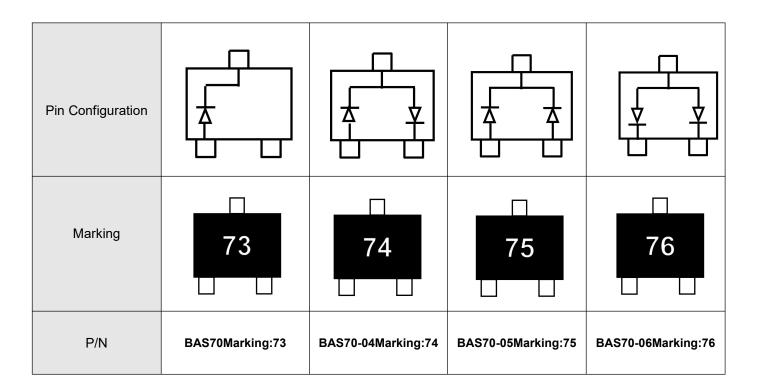


Features

- Low turn-on voltage
- Fast switching
- Also available in lead free version



Reference News





MAXIMUM RATINGS@Ta=25℃

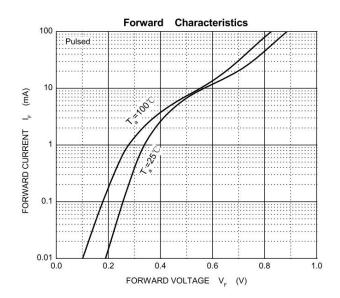
Symbol	Parameter	Value	Unit
VR	DCVoltage	70	V
lF	ForwardContinuousCurrent	70	mA
IFSM	Non-RepetitivePeakForwardSurgeCurrent@ t=8.3ms	100	mA
Po	PowerDissipation	200	mW
R _{9JA}	ThermalResistanceJunctiontoAmbient	500	°C/W
TJ	OperatingJunctionTemperatureRange	-40~+125	$^{\circ}$
Tstg	StorageTemperatureRange	-55~+150	$^{\circ}$

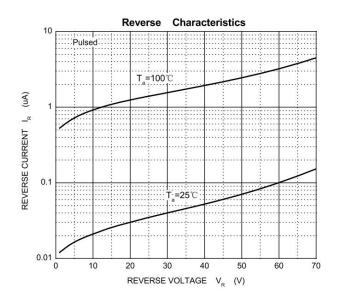
ELECTRICALCHARACTERISTICS(Ta=25 °C unless otherwise specified)

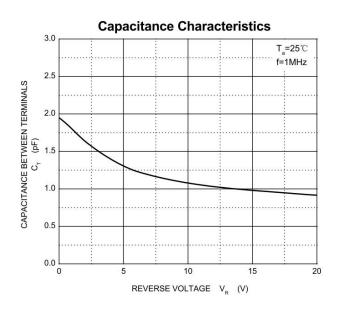
Parameter	Symbol	Testconditions	Min	Max	Unit
Reverse breakdown voltage	V _(BR)	I _R = 10 u A	70		V
Reverse voltage leakage current	l _R	V _R =50V		100	nA
Forward voltage	VF	I _F =1mA I _F =15mA		410 1000	mV
Diode cap acitance	C _D	$V_R = 0Vf = 1MHz$		2	pF
Reveres recovery time	trr	I _F = I _R = 10 mA, I _{rr} = 0.1 x I _R , R _L = 100 Ω		5	ns

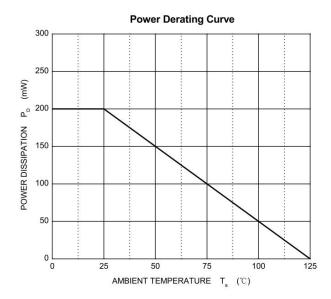


ELECTRICAL CHARACTERISTICS CURVE



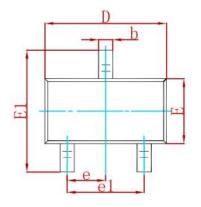


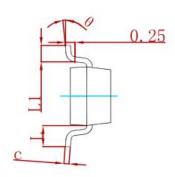


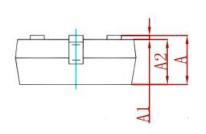




PACKAGE MECHANICAL DATA

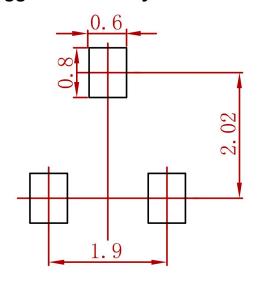






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
BAS70/-04/-05/-06	SOT-23	3000



Attention

- Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.
- MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all MSKSEMI Semiconductor products described or contained herein.
- Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer'sproducts or equipment.
- MSKSEMI Semiconductor. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with someprobability. It is possiblethat these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits anderror prevention circuitsfor safedesign, redundant design, and structural design.
- In the event that any or all MSKSEMI Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from theauthorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. Whendesigning equipment, refer to the "Delivery Specification" for the MSKSEMI Semiconductor productthat you intend to use.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Schottky Diodes & Rectifiers category:

Click to view products by MSKSEMI manufacturer:

Other Similar products are found below:

MA4E2039 MA4E2508M-1112 MBR1545CT MMBD301M3T5G RB160M-50TR D83C BAS16E6433HTMA1 BAT 54-02LRH E6327

NRVBAF360T3G NSR05F40QNXT5G NTE555 JANS1N6640 SK310-T SK34B-TP SS3003CH-TL-E GA01SHT18

CRS10I30A(TE85L,QM MA4E2501L-1290 MBRA140TRPBF MBRB30H30CT-1G BAT 15-04R E6152 JANTX1N5712-1 DMJ3940-000

SB007-03C-TB-E SK33B-TP NRVBB20100CTT4G NRVBM120LT1G NTSB30U100CT-1G VS-6CWQ10FNHM3 CRG04(T5L,TEMQ)

ACDBA1100LR-HF ACDBA1200-HF ACDBA240-HF ACDBA3100-HF CDBQC0530L-HF CDBQC0240LR-HF ACDBA260LR-HF

ACDBA1100-HF MA4E2502L-1246 10BQ015-M3/5BT NRVBM120ET1G CRS08TE85LQM PMAD1108-LF B120Q-13-F 1N5819T-G

B0530WSQ-7-F PDS1040Q-13 B160BQ-13-F SDM05U20CSP-7 B140S1F-7